Ordering number : EN8759

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

EMH2314 — General-Purpose Switching Device Applications

Features

- ON-resistance $R_{DS}(on)1$=28mΩ(typ.)
- 1.8V drive
- Halogen free compliance
- Protection Diode in

Specifications

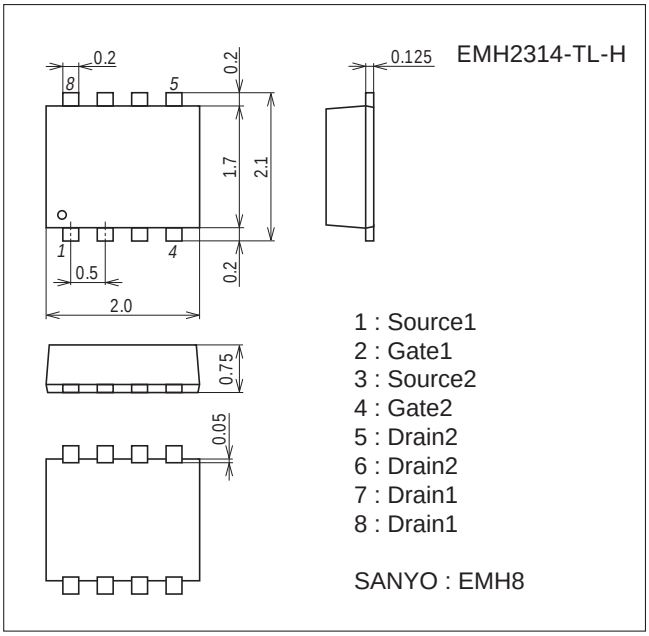
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		−12	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		-5	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	−20	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm²×0.8mm) 1unit	1.0	W
Total Dissipation	P_T	When mounted on ceramic substrate (900mm²×0.8mm)	1.2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Package Dimensions

unit : mm (typ.)

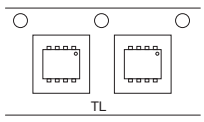
7045-002



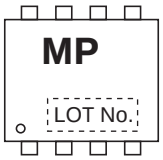
Product & Package Information

- Package : EMH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

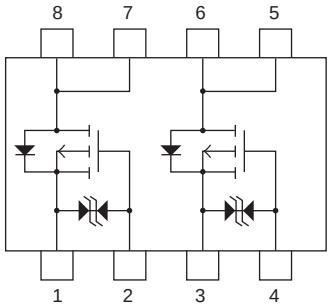
Taping Type : TL



Marking



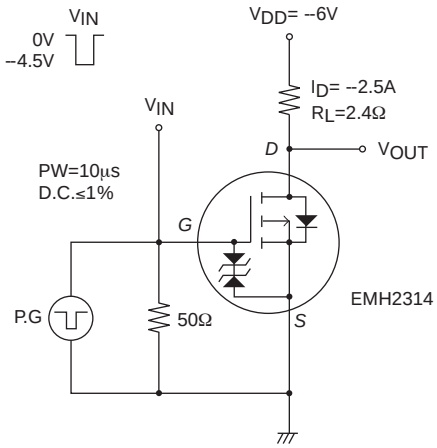
Electrical Connection



Electrical Characteristics at Ta=25°C

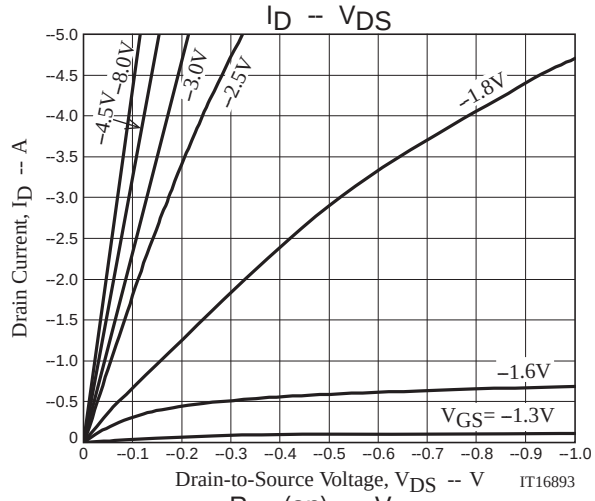
Parameter	Symbol	Conditions	Ratings			Unit
			min.	typ.	max.	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D= --1mA, V_{GS}=0V	−12			V
Zero-Gate Voltage Drain Current	I_{DSS} V	DS= −12V, V_{GS}=0V			−10	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}= -6V, I_D= --1mA	−0.4		−1.3	V
Forward Transfer Admittance	| yfs |	V_{DS}= -6V, I_D= −2.5A		11		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D= −2.5A, V_{GS}= −4.5V		28	37	mΩ
	R_{DS}(on)2	I_D= −1.5A, V_{GS}= −2.5V		53	75	mΩ
	R_{DS}(on)3	I_D= −0.5A, V_{GS}= −1.8V		133	200	mΩ
Input Capacitance	Ciss	V_{DS}= −6V, f=1MHz		1300		pF
Output Capacitance	Coss			158		pF
Reverse Transfer Capacitance	Crss			143		pF
Turn-ON Delay Time	t_{d}(on)	See specified Test Circuit.		16		ns
Rise Time	t_r			77		ns
Turn-OFF Delay Time	t_{d}(off)			79		ns
Fall Time	t_f			58		ns
Total Gate Charge	Qg	V_{DS}= −6V, V_{GS}= −4.5V, I_D= −5A		12		nC
Gate-to-Source Charge	Qgs			3n		C
Gate-to-Drain “Miller” Charge	Qgd			2n		C
Diode Forward Voltage	V_{SD}	I_S= −5A, V_{GS}=0V		−0.9	−1.2	V

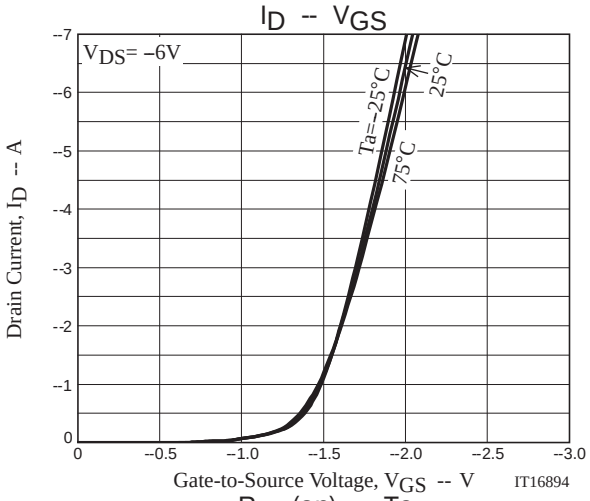
Switching Time Test Circuit

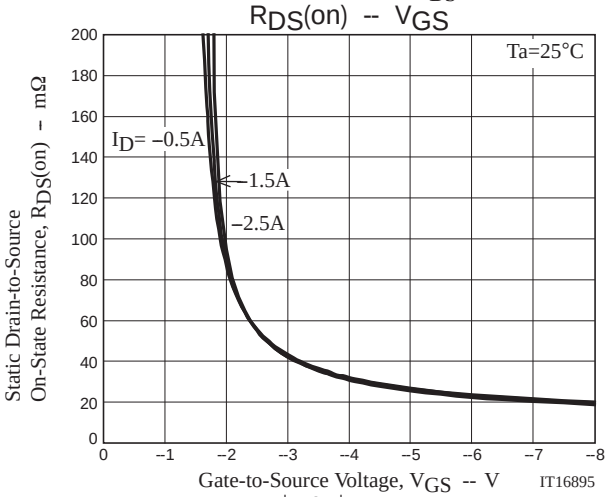


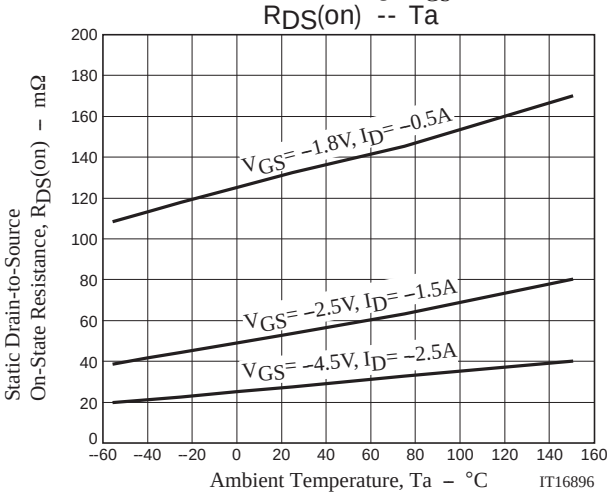
Ordering Information

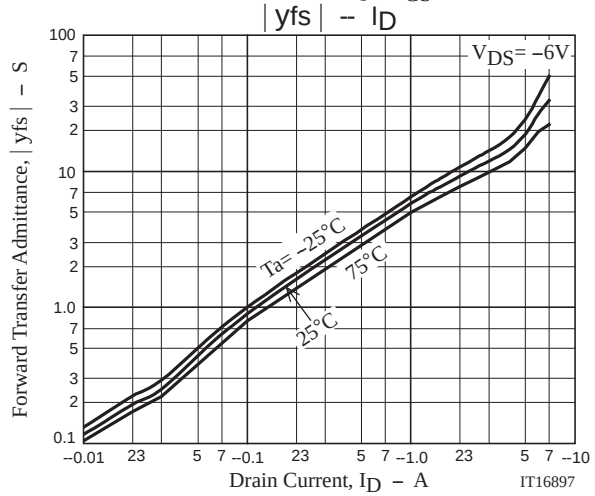
Device	Package	Shipping	memo
EMH2314-TL-H	EMH8	3,000pcs./reel	Pb Free and Halogen Free

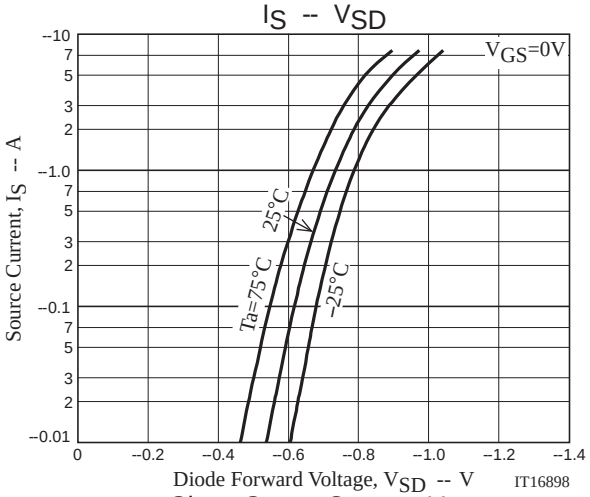

ID -- VDS
Drain Current, ID -- A
Drain-to-Source Voltage, VDS -- V
IT16893
–4.5V
–8.0V
–3.0V
–2.5V
–1.8V
–1.6V
VGS= –1.3V

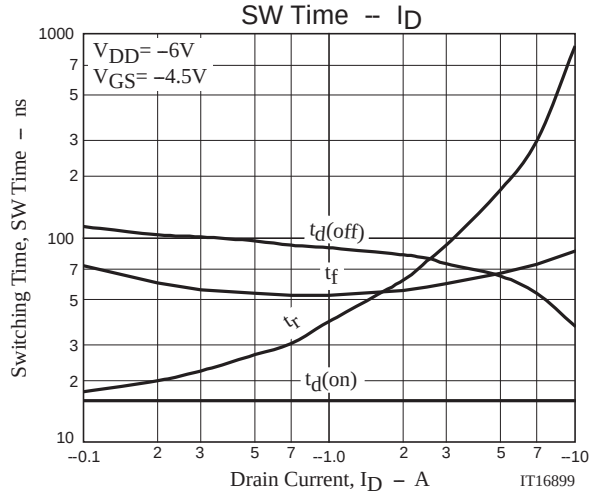

ID -- VGS
VDS= –6V
Drain Current, ID -- A
Gate-to-Source Voltage, VGS -- V
IT16894
Ta=–25°C
25°C
75°C

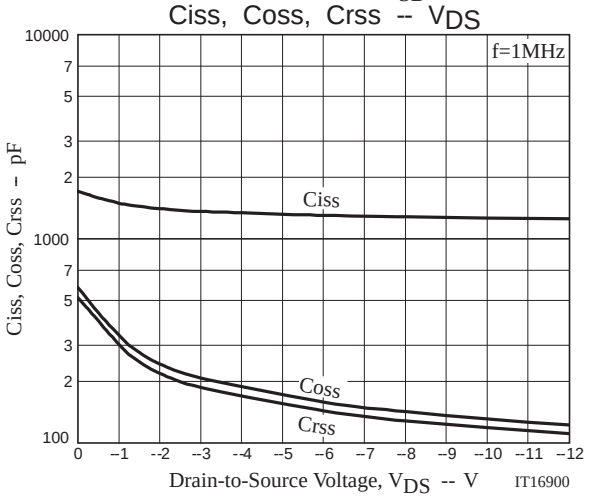

RDS(on) -- VGS
Ta=25°C
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Gate-to-Source Voltage, VGS -- V
IT16895
ID= –0.5A
–1.5A
–2.5A

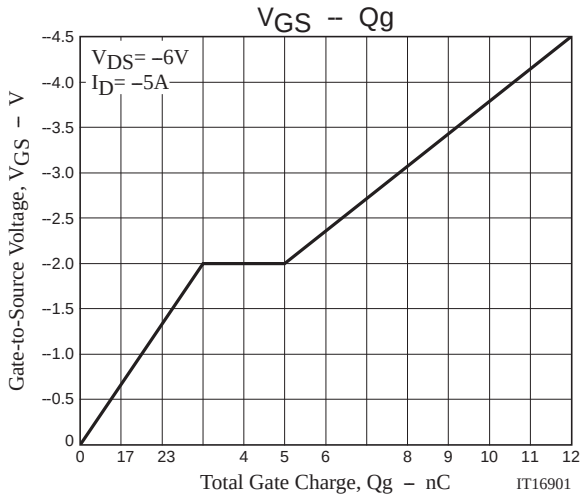

RDS(on) -- Ta
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C
IT16896
VGS= –1.8V, ID= –0.5A
VGS= –2.5V, ID= –1.5A
VGS= –4.5V, ID= –2.5A

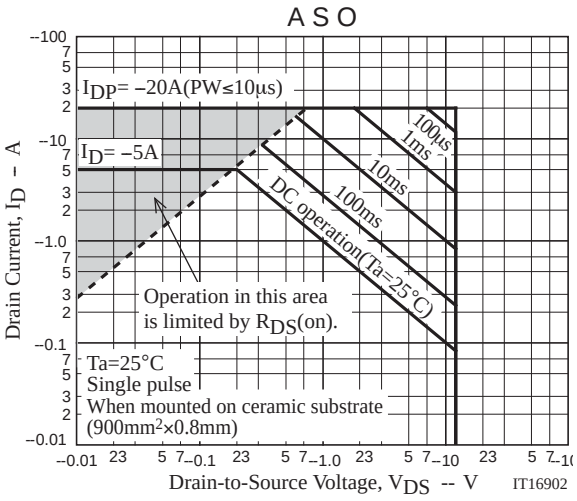

| yfs | -- ID
VDS= –6V
Forward Transfer Admittance, | yfs | – S
Drain Current, ID – A
IT16897
Ta= –25°C
25°C
75°C

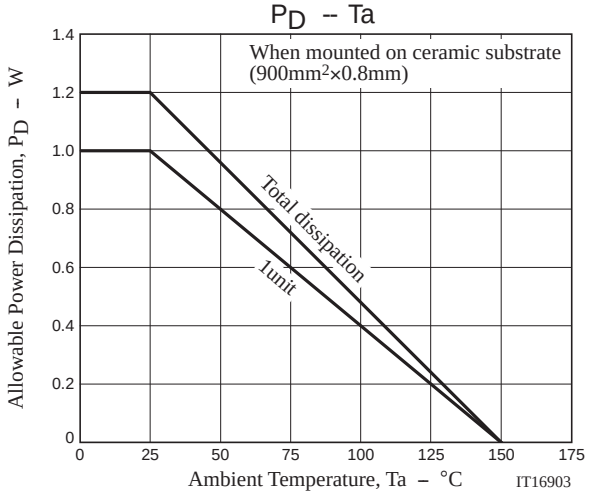

IS -- VSD
VGS=0V
Source Current, IS -- A
Diode Forward Voltage, VSD -- V
IT16898
25°C
Ta=75°C
–25°C


SW Time -- ID
VDD= –6V
VGS= –4.5V
Switching Time, SW Time – ns
Drain Current, ID – A
IT16899
td(off)
tf
tr
td(on)


Ciss, Coss, Crss -- VDS
f=1MHz
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS -- V
IT16900
Ciss
Coss
Crss


VGS -- Qg
VDS= −6V
ID= −5A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT16901


A S O
IDP= −20A(PW≤10μs)
ID= −5A
100μs
1ms
10ms
100ms
DC operation(Ta=25°C)
Operation in this area
is limited by RDS(on).
Ta=25°C
Single pulse
When mounted on ceramic substrate
(900mm2×0.8mm)
Drain Current, ID – A
Drain-to-Source Voltage, VDS -- V
IT16902


PD -- Ta
When mounted on ceramic substrate
(900mm2×0.8mm)
Total dissipation
1unit
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT16903

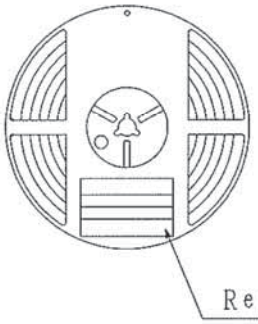
Embossed Taping Specification

EMH2314-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
EMH8	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

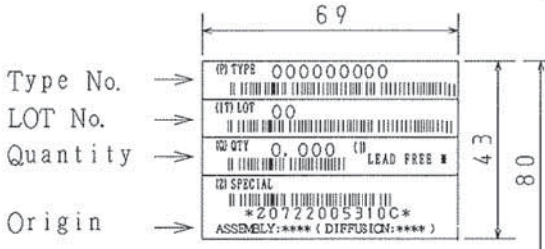
Packing method



Reel label

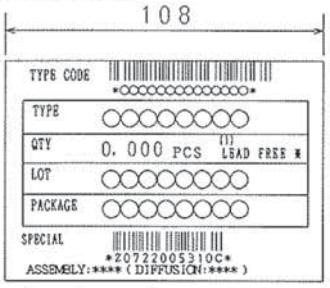
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



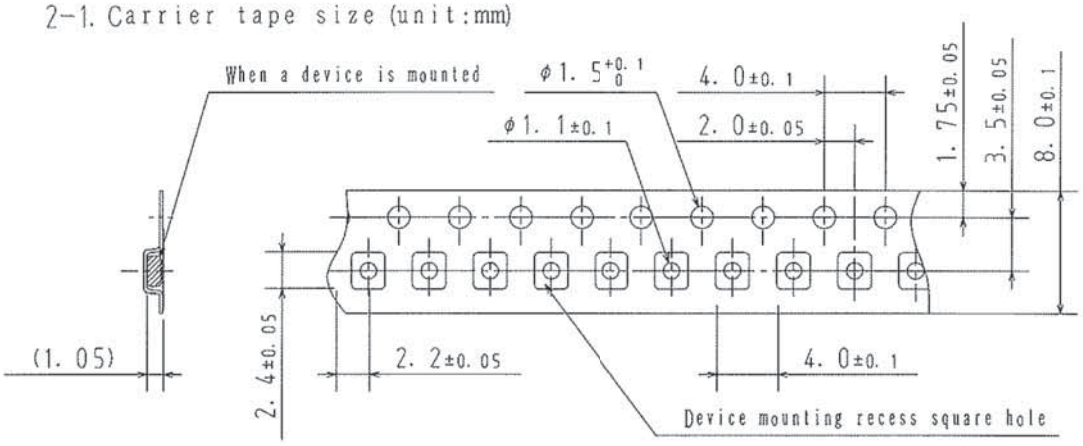
NOTE (1)

The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

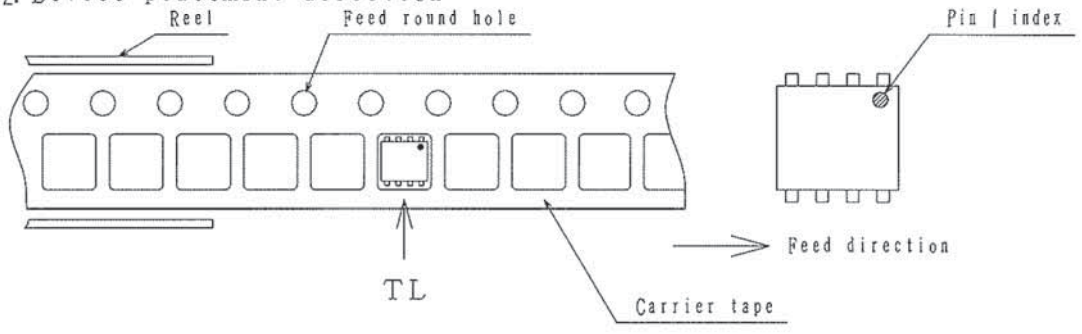
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



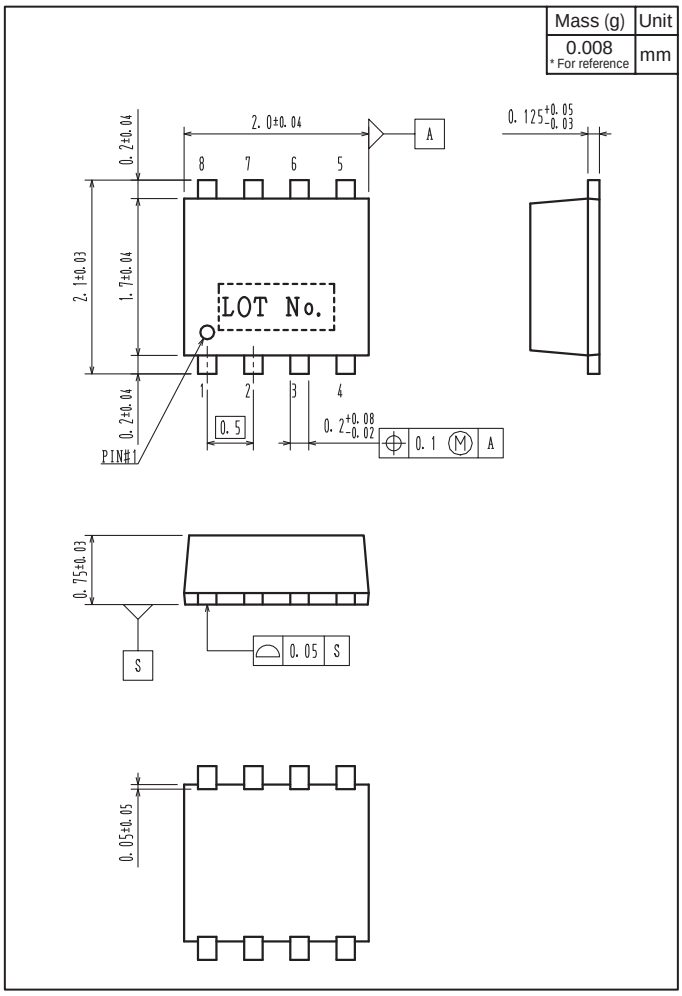
2-2. Device placement direction



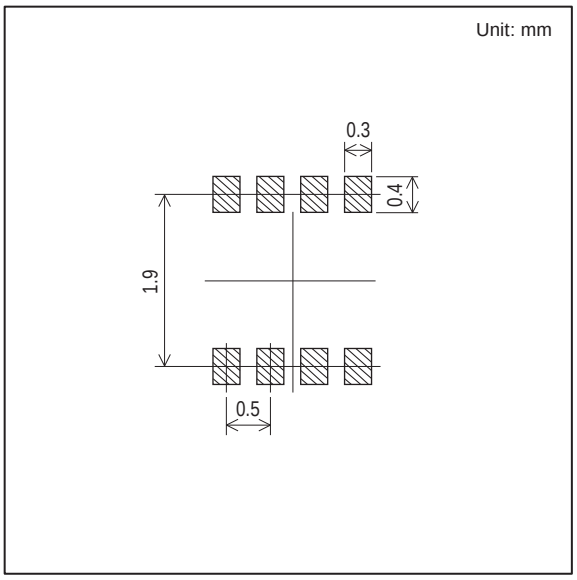
Those with pin 1 index on the feed hole side·····TL

Outline Drawing

EMH2314-TL-H



Land Pattern Example



Note on usage : Since the EMH2314 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

This catalog provides information as of May, 2012. Specifications and information herein are subject to change without notice.